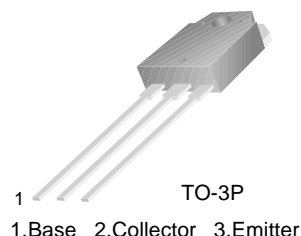


KSB817

KSB817

Audio Power Amplifier Car Booster Output Amplifier DC to DC Converter

- High Current Capability
- High Power Dissipation
- Complementary to KSD1047



PNP Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage | - 160 | V |
| V_{CEO} | Collector-Emitter Voltage | - 140 | V |
| V_{EBO} | Emitter-Base Voltage | - 6 | V |
| I_C | Collector Current (DC) | - 8 | A |
| I_{CP} | *Collector Current (Pulse) | - 16 | A |
| P_C | Collector Dissipation ($T_C=25^\circ\text{C}$) | 80 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 40 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|------------------------|--------------------------------------|--|----------|------|-------|---------------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C = - 5\text{mA}, I_E = 0$ | - 160 | | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = - 10\text{mA}, R_{BE} = \infty$ | - 140 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = - 5\text{mA}, I_C = 0$ | -6 | | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = - 80\text{V}, I_E = 0$ | | | - 0.1 | mA |
| I_{EBO} | Emitter Cut-off Current | $V_{BE} = - 4\text{V}, I_C = 0$ | | | - 0.1 | mA |
| h_{FE1} h_{FE2} | * DC Current Gain | $V_{CE} = - 5\text{V}, I_C = - 1\text{A}$ $V_{CE} = - 5\text{V}, I_C = - 6\text{A}$ | 60 20 | | 200 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = - 5\text{A}, I_B = - 0.5\text{A}$ | | | - 2.5 | V |
| $V_{BE(on)}$ | Base-Emitter ON Voltage | $V_{CE} = - 5\text{V}, I_C = - 1\text{A}$ | | | - 1.5 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE} = - 5\text{V}, I_C = - 1\text{A}$ | | 15 | | MHz |
| C_{ob} | Output Capacitance | $V_{CB} = - 10\text{V}, f = 1\text{MHz}$ | | 300 | | pF |
| t_{ON} | Turn ON Time | $V_{CC} = 20\text{V}$ | | 0.25 | | μs |
| t_F | Fall Time | $I_C = 1\text{A} = 10 \cdot I_{B1} = - 10 \cdot I_{B2}$ | | 0.53 | | μs |
| t_{STG} | Storage Time | $R_L = 20\Omega$ | | 1.61 | | μs |

* Pulse Test: $PW = 20\mu\text{s}$

h_{FE} Classification

| Classification | O | Y |
|----------------|----------|-----------|
| h_{FE1} | 60 ~ 120 | 100 ~ 200 |

Typical Characteristics

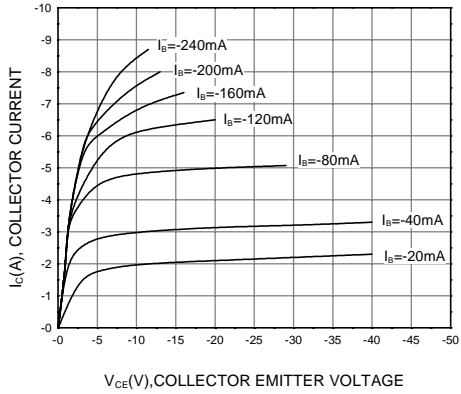


Figure 1. Static Characteristic

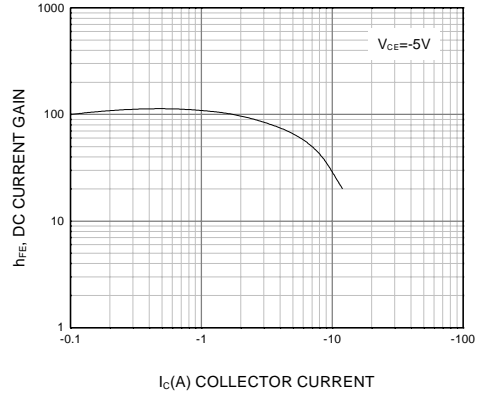


Figure 2. DC current Gain

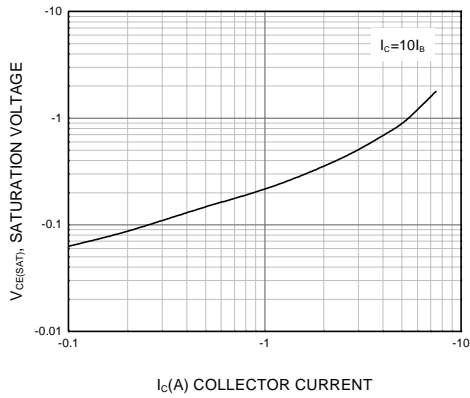


Figure 3. Collector-Emitter Saturation Voltage

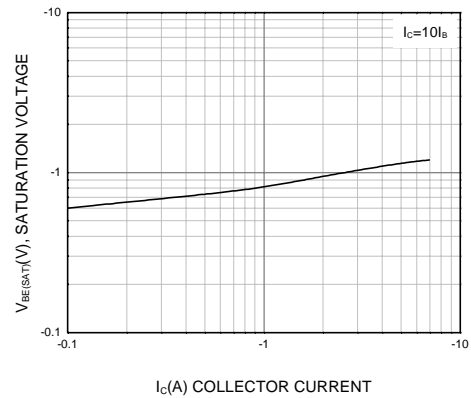


Figure 4. Base-Emitter Saturation Voltage

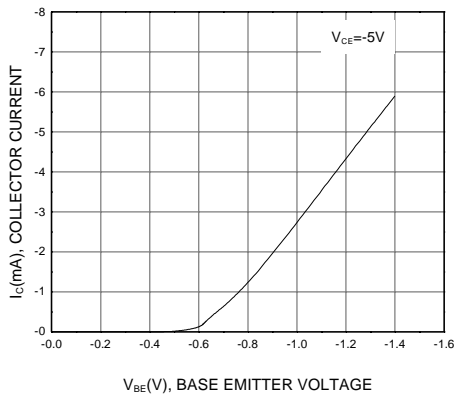


Figure 5. Base-Emitter On Voltage

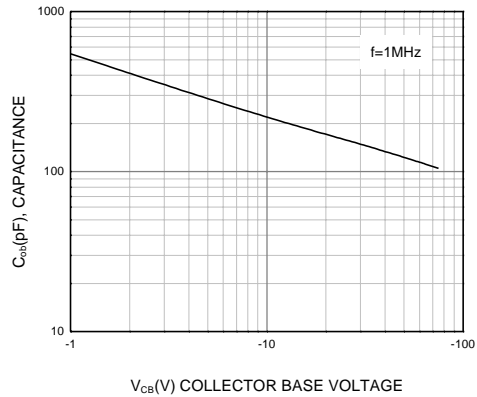


Figure 6. Collector Output Capacitance

Typical Characteristics (Continued)

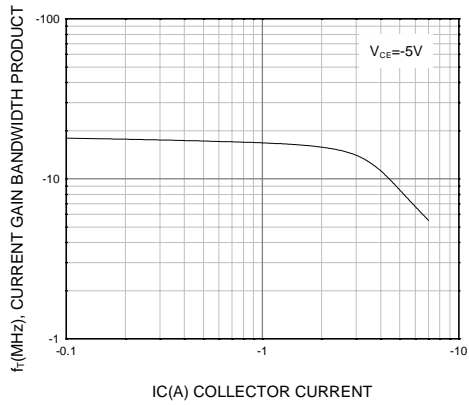


Figure 7. Current Gain Bandwidth Product

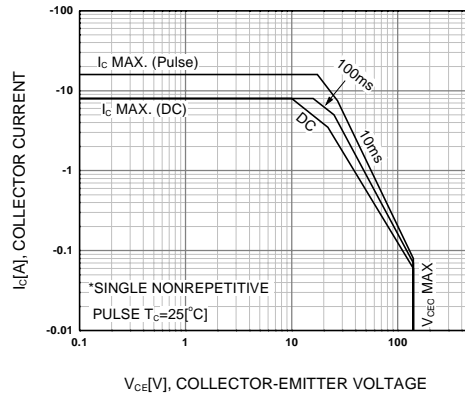


Figure 8. Safe Operating Area

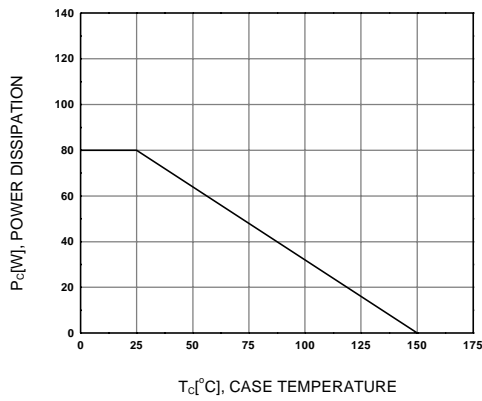
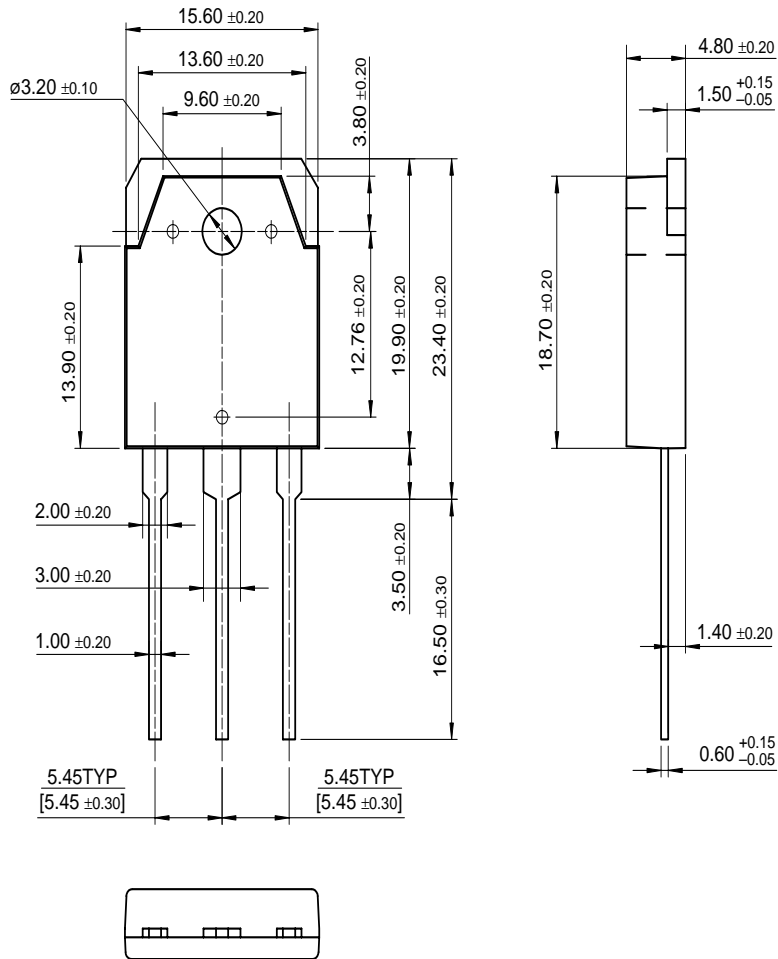


Figure 9. Current Gain Bandwidth Product

Package Dimensions

KSB817

TO-3P



Dimensions in Millimeters

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|----------------------|---------------|-------------|
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| E ² CMOS™ | PowerTrench® | VCX™ |
| FACT™ | QFET™ | |
| FACT Quiet Series™ | QS™ | |
| FAST® | Quiet Series™ | |
| FASTr™ | SuperSOT™-3 | |
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